

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A semiconductor device comprising a MIS-type field-effect-transistor (FET), said MIS-type FET including:
  - a silicon substrate;
  - an insulating film formed on said silicon substrate and containing silicon and at least one of nitrogen and oxygen;
  - a metal oxide film formed on said insulating film and containing silicon and hafnium;
  - and
  - a gate electrode formed on said metal oxide film, wherein:
    - a silicon molar ratio ( $\text{Si}/(\text{Si}+\text{Hf})$ ) in said ~~[[metal]]~~ metal oxide film is not lower than 2% and not higher than 15%; and
    - said metal oxide film has a dielectric constant in a range from about 20 to about 24.
2. (Original) The semiconductor device according to claim 1, wherein said metal oxide film includes therein polycrystalline particles having diameters of not smaller than 30nm and smaller than 100nm.
3. (Original) The semiconductor device according to claim 1, wherein said MIS-type FET has a silicon nitride film on said metal oxide film.
- 4 - 20. (Cancelled).
21. (New) The semiconductor device according to claim 1, wherein said dielectric constant of said metal oxide film is about 24.
22. (New) The semiconductor device according to claim 1, wherein crystal grains of said metal oxide film are substantially free of the silicon.

23. (New) The semiconductor device according to claim 22, wherein the silicon is located substantially at grain boundaries of the crystal grains.
24. (New) The semiconductor device according to claim 22, wherein said crystal grains are HfO<sub>2</sub> crystals.
25. (New) The semiconductor device according to claim 22, wherein said crystal grains have diameters in a range from about 30 nm to about 100 nm.